Calculation of Performance Parameters and Reliability Aspects of Phase Shifted Semi Bridgeless Interleaved Boost Converter

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Abstract— Hybrid Electric Vehicles (HEVs) require a power modulator like an AC-DC converter at the charging end of the vehicle. The converter induces harmonics and distortion in the supply current due to the presence of nonlinear devices in its topology. This results in reduction of Power Factor (PF) and Efficiency. Hence, there is a need for implementation of a Power Factor Correction (PFC) circuit along with a rectifier to improve the performance of the charger. Among the various topologies mentioned in the literature, Bridgeless Interleaved and Phase Shifted Semi Bridgeless Interleaved PFC topologies are optimal solutions for the problem. This paper mainly focuses on the Performance Parameters and Reliability aspects of both the topologies operating in Continuous Conduction Mode (CCM). The Reliability aspects are based upon MILHDBK-217F standards. The topologies are simulated using MATLAB and the results are recorded. This paper is an effort to grade both the converters on the basis of reliability and other performance parameters.

Index Terms— AC – DC Converters, Hybrid Electric Vehicles, PSIBC, Reliability, Power loss.

I. INTRODUCTION

The main purpose of an AC - DC converter in the charging system of HEVs is to rectify the given AC supply and generate a constant DC supply. But the waveform is distorted due to the induced harmonics [1]. Thereby the power factor is also compromised. Therefore there is a need for a highly efficient converter which eliminates these drawbacks [2]. The topologies basically consist of a rectification part which converts the AC supply to a pulsating DC followed by a boost converter to enhance the output voltage. They are also provided with a bypass capacitor to filter the output ripple. Bridgeless Interleaved PFC and Phase Shifted Semi-Bridgeless Interleaved Boost PFC topologies are proposed for improving the performance of the charger in HEVs [3, 4].

In Bridgeless Interleaved (BLIL) boost topology, the diode bridge rectifier is eliminated so that the diode bridge losses [5], which are very significant at higher power levels, are minimized and thus higher efficiency is achieved. By employing the interleaving technique in the topology, effective ripple cancellation can also be achieved [6]. As a result, the Total Harmonic Distortion (THD) is reduced in this topology [7]. In Phase Shifted Semi-Bridgeless Interleaved Boost Converter (PSIBC) [8], four slow diodes are added to the bridgeless configuration to link the ground of the circuit to the input line. It employs the phase shifting technique to achieve EMI cancellation and interleaving operation to reduce the ripple content. The Electro Magnetic Interference (EMI), which is a hidden problem in BLIL, is reduced in this converter [9, 10].

The above mentioned topologies are also analyzed from the reliability point of view as reliability plays an important role in estimating the rate of system failures, warranty and the probability of functionality of a product for a defined period of time under specific conditions without any failure.

II. PHASE SHIFTED SEMI BRIDGELESS IBC

A. Circuit Diagram

B. Operation

During the positive half cycle of the supply, switches Q1 and Q2 are turned on. Thus the current flows along the path L1 - Q1 - Q2 and returns to the mains via L2. Thus the inductors L1 and L2 are charged up during this interval. When Q1 - Q2 are turned off, due to large rate of change of current flow, the voltage across the inductor reverses its polarity to oppose the large change in di/dt and tries to

maintain current in the same direction. Thus inductors L1 and L2 starts discharging through D1 - load and returns to the mains through the body diode of Q2 and partially through Db.

In the interleaved converter, switches Q3 and Q4 are turned on after a phase delay of 180 degrees. The current flows along the path L3 - Q3 - Q4 returns to the mains via L4. Thus the inductors L3 and L4 are charged up during this interval. When Q3-Q4 are turned off , the inductors L3 $\,$ and L4 starts discharging through D3, load and returns to the mains through the body diode of Q4 and partially through Dd. The same can also be explained for the negative half cycle of the supply.

III. PERFORMANCE PARAMETERS

A. Total Harmonic Distortion

Total Harmonic Distortion of input current is defined as the measure of harmonic content present in the input current. It is the measure of distortion in the input current waveform when compared with the desired waveform. Mathematically it is defined follows, as

$$THD = \frac{\sqrt{\sum_{n=2}^{\infty} l^2_{n,rms}}}{l_{1,rms}}$$
(1)

where,

 I_n rms = rms value of nth harmonic component of the input current, $2 < n < \infty$.

 I_1 rms = rms value of the fundamental component of the input current.

B. Supply Power Factor

Power Factor (PF) is defined as the product of displacement factor and purity factor.

$$PF = K_d \ge K_p \tag{2}$$
$$K_d = \cos \theta \tag{3}$$

 $K_d = \cos \theta$

where.

 Θ = angular displacement between input voltage and current waveforms

 $K_d = Displacement Factor$

K_p = Purity Factor

C. Efficiency

Efficiency can be defined as the ratio of the output power delivered to the input power supplied to the converter. Mathematically, it is represented as follows,

$$\eta = \frac{p_{in} - p_{loss}}{p_{in}} \times 100 \tag{4}$$

D. Component Losses

1) MOSFET (Switch)

The power loss of a MOSFET comprises of the loss due to frequent switching of the device (PSW(MOSFET)) and the losses due to conduction (PCOND (MOSFET)) [11].

$$P_{\text{COND (MOSFET)}} = I^2_{\text{drain (rms)}} \times R_{\text{DS (on)}}$$
(5)

 $P_{SW(MOSFET)} = 0.5 \times V_{DS} \times I_{drain(rms)} \times f_{sw} \times (t_{on}+t_{off})$ (6)Where. **D** 1 *C* 2 A A MORET

I drain (rms)	- RMS current through the MOSFET
RDS (on)	- On state Drain – Source resistance
Vds	- Drain – Source forward voltage
f _{sw}	- Switching frequency
ton	- Turn on time of MOSFET

- Turn off time of MOSFET toff

2) Fast Diode

The power loss of a diode (P_{DIODE}) is due to the reverse recovery loss (P_{rr(DIODE)}), diode conduction loss (P_{COND (DIODE)}) and diode switching loss(P_{SW (DIODE)}).

$$P_{\text{DIODE}} = P_{\text{rr}(\text{DIODE})} + P_{\text{COND}(\text{DIODE})} + P_{\text{SW}(\text{DIODE})}$$
(7)

E. Reliability Aspects

1) Reliability Function

The probability of a component operating under specified conditions for a defined period of time can be estimated mathematically as

 λ is the failure rate constant during the useful life period of the device.

 $R(t) = e^{-\lambda t}$

2) Failure Rates

Table 1: Mathematical equations for calculation of Failure rate	Table 1: Mathematical	equations f	or calculation	of Failure rate
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Device	Mathematical Equation for Failure rate λ_p (Failures/10 ⁶ Hours) [12]
MOSFET	$\lambda_b {\times} \pi_A {\times} \pi_T {\times} \pi_Q {\times} \pi_E$
Fast Diode	$\lambda_{b\times}\pi_{S\times}\pi_{C\times}\pi_{T\times}\pi_{Q\times}\pi_{E}$
Inductor	$\lambda_b{\scriptstyle\times}\pi_Q{\scriptstyle\times}\pi_E$
Capacitor	$\lambda_b {\times} \pi_Q {\times} \pi_E {\times} \pi_{CV}$
Resistor	$\lambda_b{}_\times\pi_Q{}_\times\pi_E{}_\times\pi_P{}_\times\pi_S$

where,

 λ_b - Base failure rate of the device

 π_A – Application factor

- $\pi_{\rm T}$ Temperature factor
- π_0 Quality factor
- $\pi_{\rm E}$ Environment factor
- π_{S} Voltage stress factor
- $\pi_{\rm C}$ Contact construction factor

(8)

IV. RESULTS

The following are the results obtained on simulation of BLIL and PSIBC topologies [13, 14]:

Table 2: Design parameters for PSIBC and BLIL topologies		
Design Parameters for PSIBC and BLIL		
Input supply	230 V	
Supply frequency	50 Hz	
L1,L2,L3,L4	667 µH	
R (load)	50 Ω	
С	150 μF	
Switching frequency	25 kHz	
Duty Ratio	0.5	

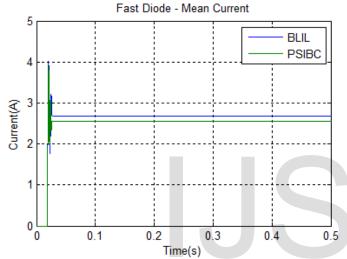
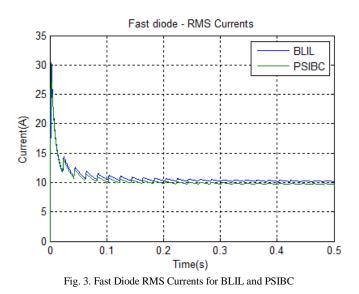
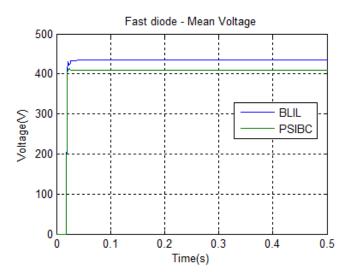
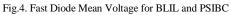
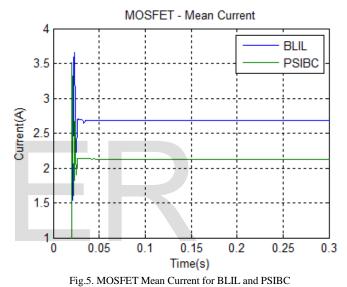


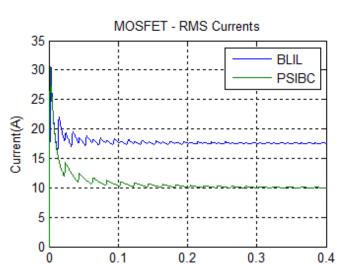
Fig. 2. Fast Diode Mean Currents for BLIL and PSIBC











Time(s)

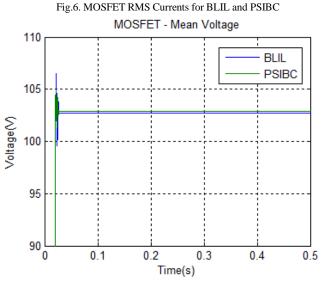


Fig.7. MOSFET Mean Voltages for BLIL and PSIBC

On examining the graphical results, it can be inferred that the current and voltage levels in the components are higher in the case of BLIL topology than PSIBC. This is the foremost cause of high power loss in BLIL topology.

Performance Parameters - PSIBC		
Supply power factor	0.86432734	
Total Harmonic Distortion (%)	58.18	
Supply voltage peak (V)	325	
Supply power (W)	7140.7267	
Mean output voltage (V)	570.4076	
Mean load current (A)	11.592	
Output power (W)	6612.1648	
Efficiency (%)	92.5979	

Hence, the performance parameters of a 6.6kW Charger for HEVs with Phase Shifted Semi Bridgeless Interleaved Boost AC – DC Converter are tabulated in table 3.

V. ANALYSIS AND COMPARISON OF POWER LOSS AND RELIABILITY ASPECTS OF PSIBC AND BLIL TOPOLOGIES

The following devices manufactured by the leading manufacturers are selected to estimate the reliability and power loss of BLIL and PSIBC topologies. All the selected devices are RoHS (Restriction of Hazardous Substances Directive) compliant and qualified by AEC (Automotive Electronics Council) and JEDEC (Joint Electron Device Engineering Council).

Table 4: Components for estimating the Reliability and Power loss of BLIL and

PSIDC			
Component	Specification		
Switch (MOSFET)	IPB60R099CP		
Fast Diode	IDB06S60C		
Inductor	Kool mu 77071 core type		
Capacitor	EKXJ451ELL820		

Table 5: MOSFET Specifications

IPB60R099CP – Infineon MOSFET – Low Frequency (Less than 400MHz) – Specifications			
Parameter	Value	Remark	
R _{DS} ON	0.09 Ω		
$T_{ON} + T_{OFF}$	80 ns		
λ_b (Base Failure Rate)	0.012	MOSFET	
Π_A (Application Factor)	10	Rated Power $\ge 250W$	
Π_Q (Quality Factor)	5.5	Assuming the worst case – Lower Quality	
$\Pi_{\rm E}$ (Environment Factor)	6	G _F	
Π_{T} (Temperature Factor)	BLIL – 245.9066 PSIBC – 68.01547		
T _a (Ambient Temperature)	27°C		

Table 6: Specifications of Fast Diode IDB06S60C – Infineon Diode – Low Frequency (Less than 400MHz) – Specifications [15]		
Parameter	Value	Remark
$T_{ON} + T_{OFF}$	10 ns	
Forward Voltage drop	1.5 V	
λ_b (Base Failure Rate)	0.025	Fast Recovery type
$\Pi_{\rm S}$ (Electrical Stress Factor)	0.09729	
Π_Q (Quality Factor)	5.5	Assuming the worst case – Lower Quality
$\Pi_{\rm E}$ (Environment Factor)	6	G _F
Π_{T} (Temperature Factor)	BLIL – 163.52246 PSIBC – 143.0755	Fast Recovery type
T _a (Ambient Temperature)	27°C	

EKXJ451ELL820 – Capacitor – Specifications			
Parameter	Value	Remark	
Туре	CQ,CQR	Capacitor, Fixed Plastic Dielectric (Hermetically sealed in metal, ceramic or glass cases)	
λ_b (Base Failure Rate)	0.00051	CQ,CQR	
Π_Q (Quality Factor)	10	Unknown/Commercia Purposes	
$\begin{array}{c} \Pi_{\rm E} ({\rm Environment} \\ {\rm Factor}) \end{array}$	6	G _F	
Π_{CV}	0.06969	$(0.34*C^{0.18})$	
T _a (Ambient Temperature)	27°C		

Table 8: Specifications of Inductor			
Kool mu 77071 – Inductor – Specifications			
Parameter	Value	Remark	
λ_b (Base Failure Rate)	0.049	High Power, High Pulse	
Π_Q (Quality Factor)	3.0	Lower Quality	
Π _E (Environment Factor)	6	G _F	
T _a (Ambient Temperature)	27°C		

The power loss calculations, power factor and efficiency of BLIL and PSIBC are recorded as follows:

Table 9: Comparison of Power loss, Power factor, Efficiency of BLIL and PSIBC

Feature	BLIL	PS IBC
Switch Losses (MOSFET * 4)	110.7208 W	36.089 W
Fast Diode Losses (Diode * 4)	18.44596 W	17.512 W
Power Factor	0.90200	0.86432734
Efficiency	91.752%	92.5979%

Hence, it is mathematically justified that BLIL topology suffers due to high power loss and reduced efficiency when compared with PSIBC.

Table 10: Comparison of Reliability and Failure rates of BLIL

Feature	PSIBC	BLIL
$\lambda_p MOSFET$	269.3412648	973.7904207
λ_p Diode	11.483864	13.12500806
λ_p Inductor	1.00128	1.00128
λ_p Capacitor	3.55E-3	3.55E-3

λ_p Resistor	0.0297	0.0297
λ_p System	1127.338885	3951.700085
MTBF (Hours)	887.0447	253.0556415

The base failure rates of individual components and of the whole system are calculated and tabulated in table 10 along with the Mean Time between Failures (MTBF). From the table it is mathematically justified that the overall failure rate of the system is less in the case of PSIBC. Hence, It is highly reliable for the specified applications.

VI. CONCLUSION

On comparison of both the topologies, it is inferred that though there is a marginal decrease in power factor in PSIBC due to the harmonics induced by the slow diodes, its major features such as reduced EMI noise, high reliability and improved efficiency proves it to be an optimal topology for implementation in HEV chargers than BLIL. Performance parameters and reliability aspects based on MILHDBK-217F standards are calculated and also mathematical justification for the low power loss and high reliability in the case of PSIBC topology is also provided in this paper. Hence it is mathematically proved that Phase Shifted Semi Bridgeless Interleaved Boost AC – DC converter is a highly reliable topology for use in the charging system of HEVs.

VII. REFERENCES

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